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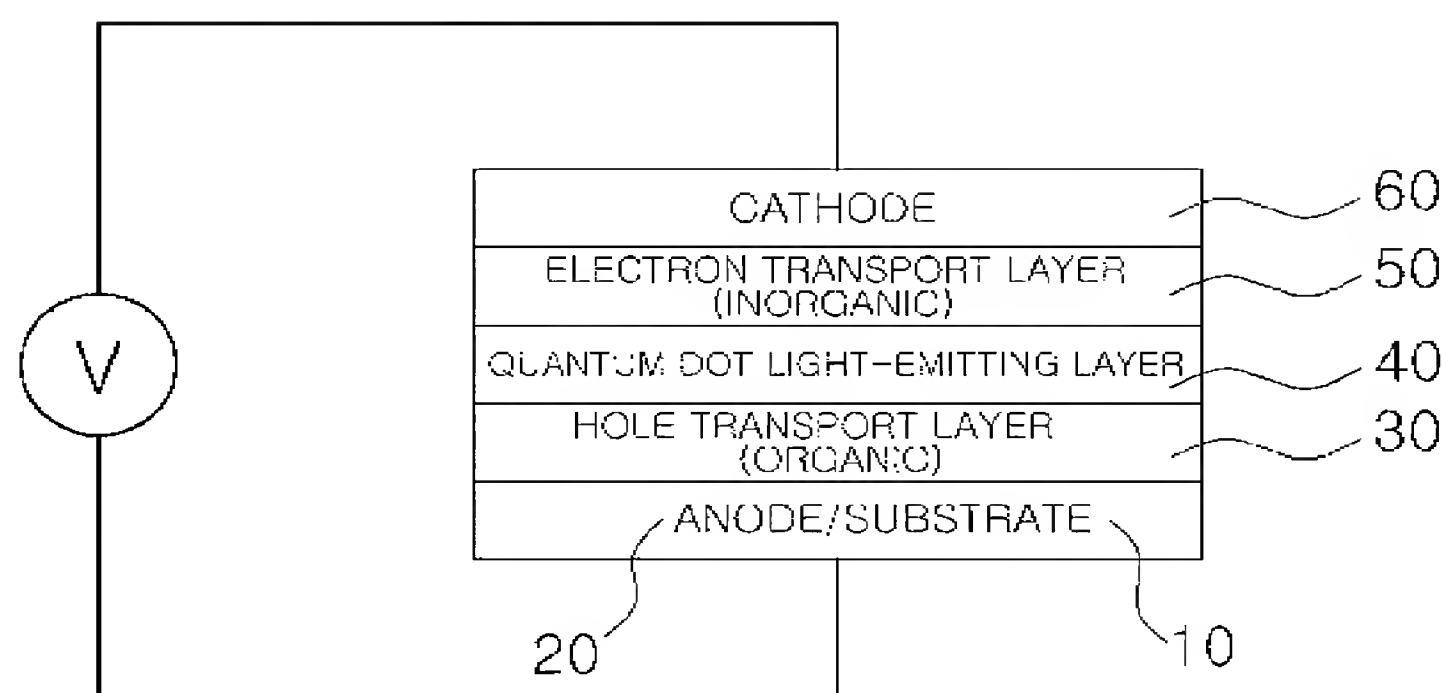
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(54) Title: QUANTUM DOT LIGHT -EMITTING DIODE COMPRISING INORGANIC ELECTRON TRANSPORT LAYER



(57) Abstract: Disclosed herein a quantum dot light-emitting device which has an inorganic electron transport layer. According to the device, an electron transport layer formed by an inorganic materials, thereby providing a high electron transport velocity or electron density and improving a light emitting efficiency. Further, interlayer resistance between electrode and organic-electron transporting layer or between quantum dot light-emitting layer and organic-electron transporting layer is prohibit, thus increasing a light emitting efficiency of diode.

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